



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

2SA2016/2SC5569 — PNP / NPN Epitaxial Planar Silicon Transistor

DC / DC Converter Applications

Applications

- Relay drivers, lamp drivers, motor drivers, flash

Features

- Adoption of FBET and MBIT processes
- Low collector-to-emitter saturation voltage
- Ultrasmall package facilitates miniaturization in end products
- High allowable power dissipation
- Large current capacity
- High-speed switching

()2SA2016

Specifications

Absolute Maximum Ratings at Ta=25°C

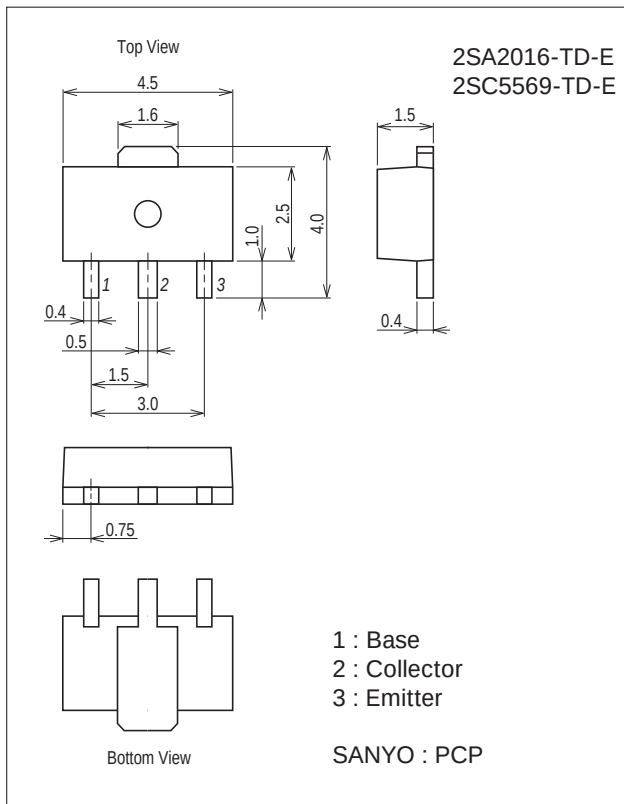
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(-50)100	V
Collector-to-Emitter Voltage	V _{CES}		(-50)100	V
Collector-to-Emitter Voltage	V _{CEO}		(-)50	V
Emitter-to-Base Voltage	V _{EBO}		(-)6	V

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Package Dimensions

unit : mm (typ)

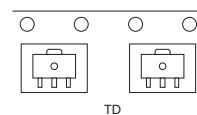
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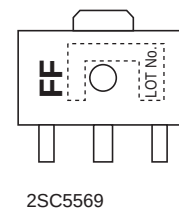
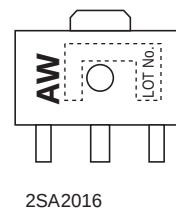
Product & Package Information

- Package : PCP
- JEITA, JEDEC : SC-62, SOT-89, TO-243
- Minimum Packing Quantity : 1,000 pcs./reel

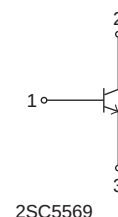
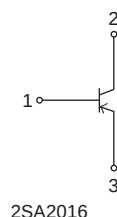
Packing Type: TD



Marking



Electrical Connection



SANYO Semiconductor Co., Ltd.

<http://www.sanyosemi.com/en/network/>

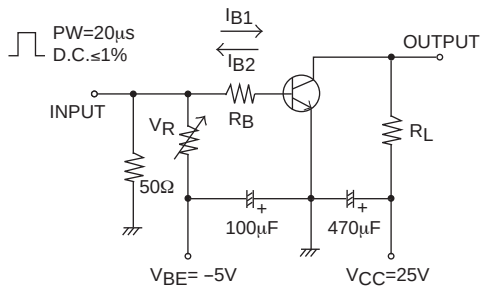
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Parameter	Symbol	Conditions	Ratings	Unit
Collector Current	I_C		(-)7	A
Collector Current (Pulse)	I_{CP}		(-)10	A
Base Current	I_B		(-)1.2	A
Collector Dissipation	P_C	When mounted on ceramic substrate (250mm ² ×0.8mm)	1.3	W
		$T_c=25^{\circ}\text{C}$	3.5	W
Junction Temperature	T_j		150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics at $T_a=25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40\text{V}$, $I_E=0\text{A}$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4\text{V}$, $I_C=0\text{A}$			(-)0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)2\text{V}$, $I_C=(-)500\text{mA}$	200		560	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10\text{V}$, $I_C=(-)500\text{mA}$		(290)330		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10\text{V}$, $f=1\text{MHz}$		(50)28		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)1}$	$I_C=(-)3.5\text{A}$, $I_B=(-)175\text{mA}$		(-230)160	(-390)240	mV
	$V_{CE(sat)2}$	$I_C=(-)2\text{A}$, $I_B=(-)40\text{mA}$		(-240)110	(-400)170	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)2\text{A}$, $I_B=(-)40\text{mA}$		(-)0.83	(-)1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}$, $I_E=0\text{A}$	(-50)100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=(-)100\mu\text{A}$, $R_{BE}=0\Omega$	(-50)100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{mA}$, $R_{BE}=\infty$	(-)50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu\text{A}$, $I_C=0\text{A}$	(-)6			V
Turn-On Time	t_{on}	See specified Test Circuit.		(40)30		ns
Storage Time	t_{stg}			(225)420		ns
Fall Time	t_f			25		ns

Switching Time Test Circuit

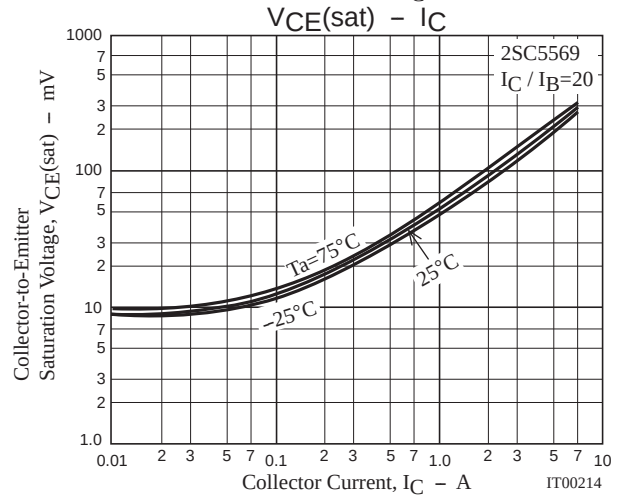
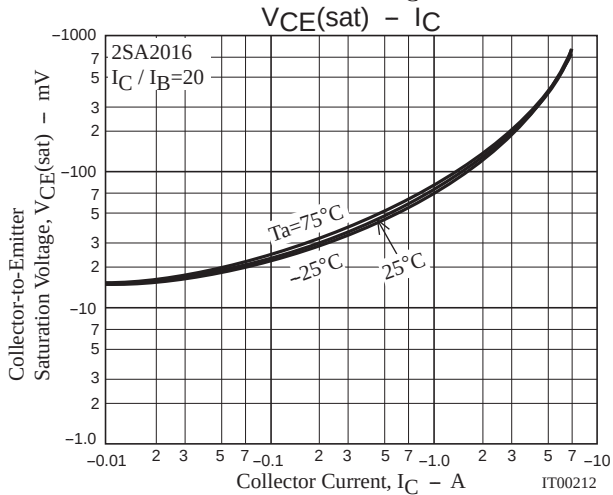
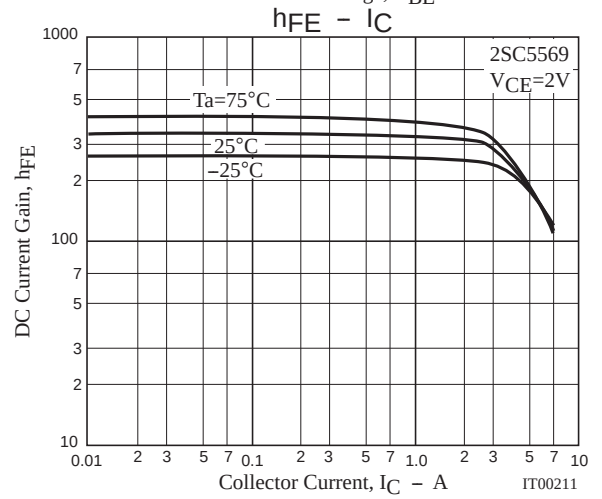
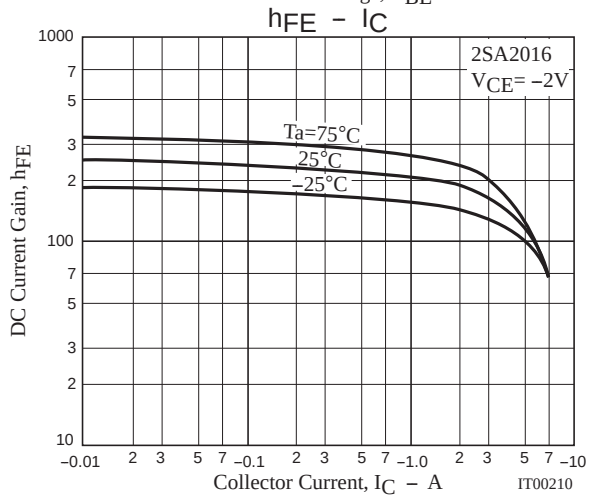
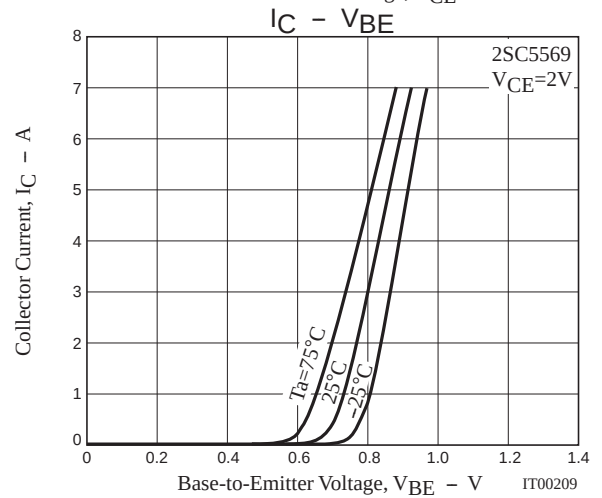
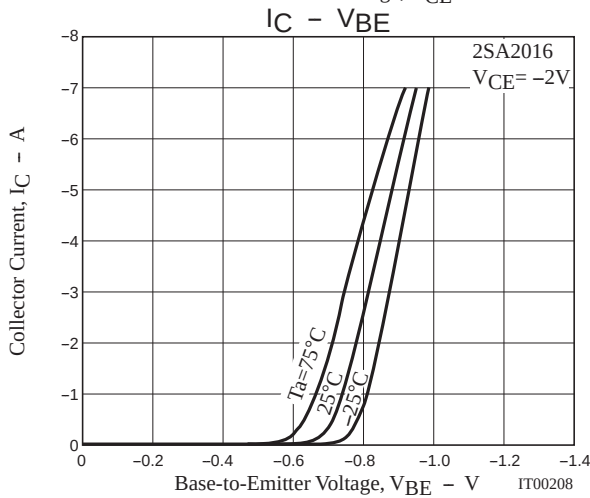
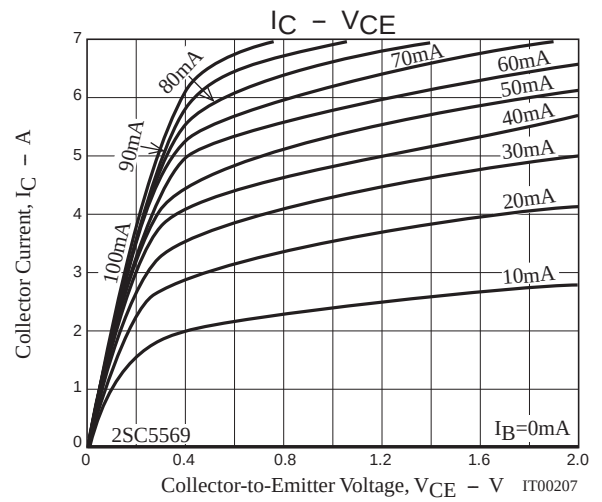
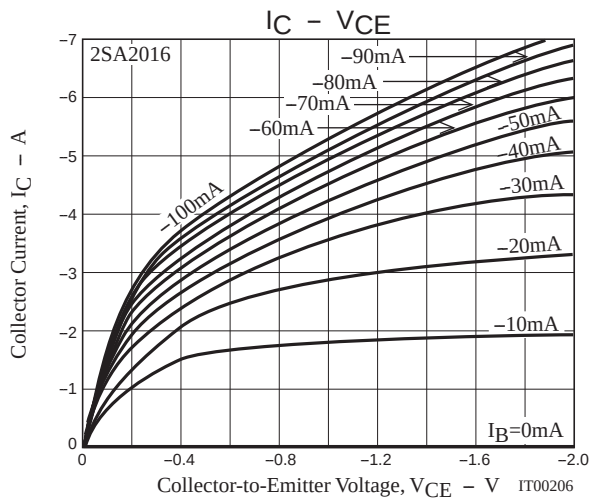


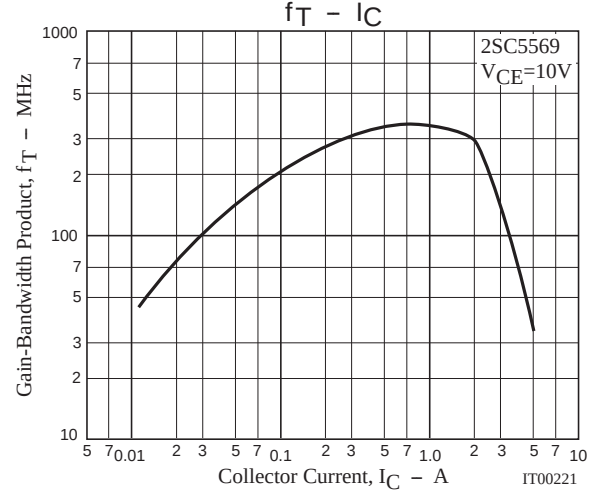
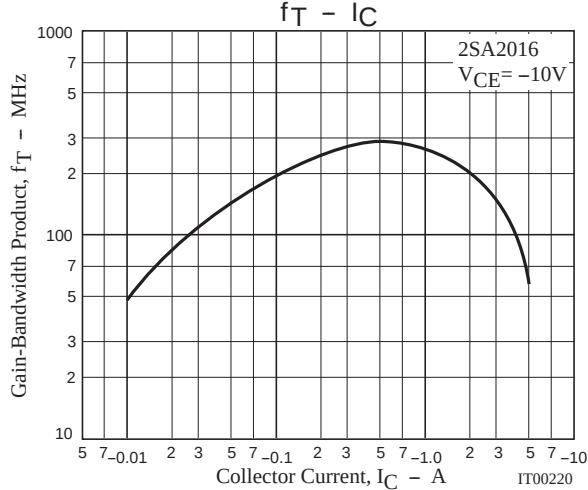
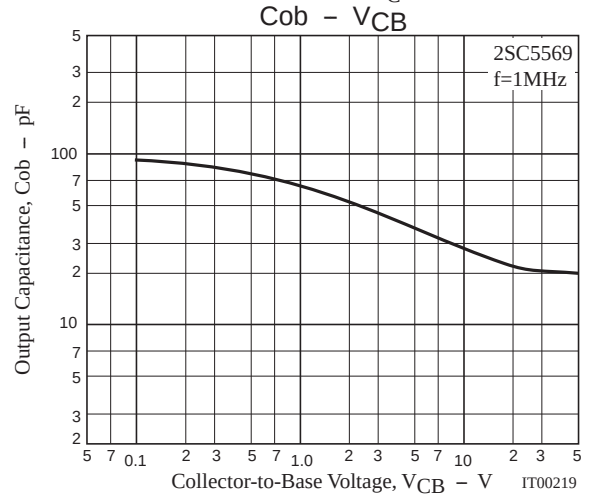
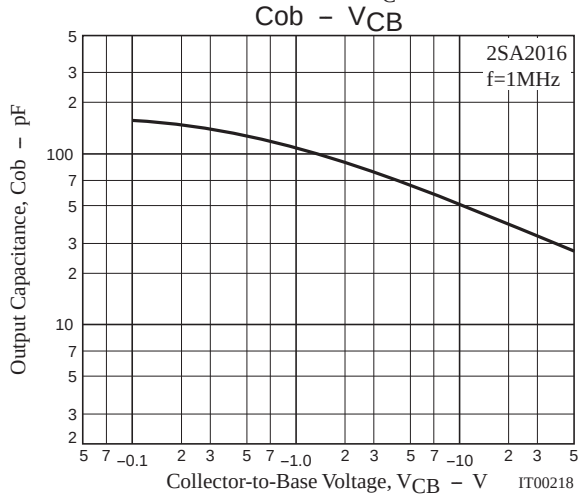
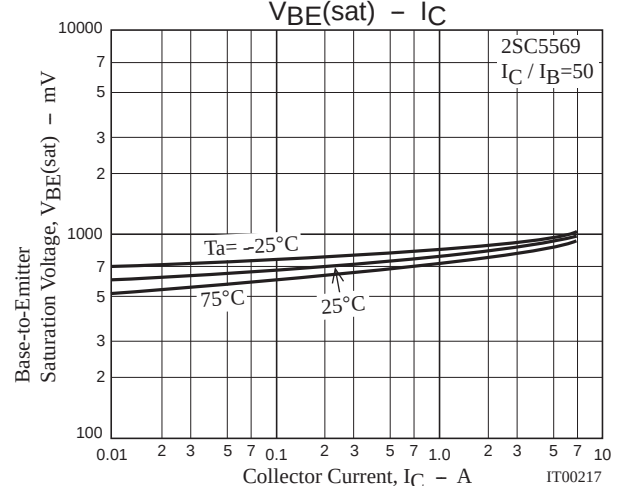
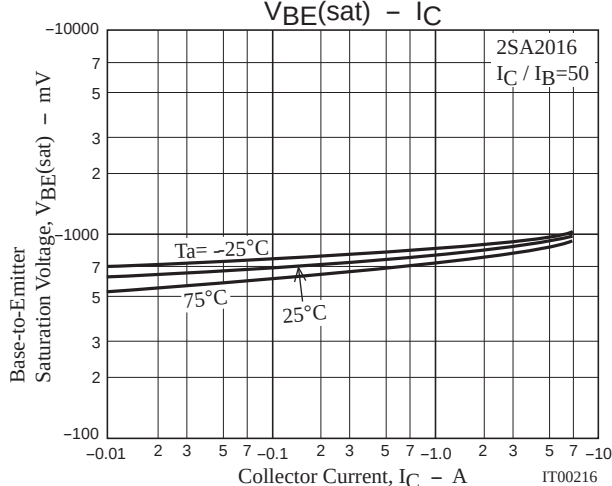
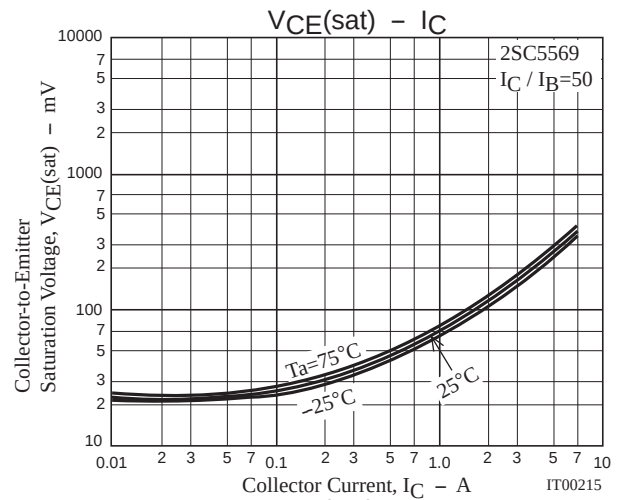
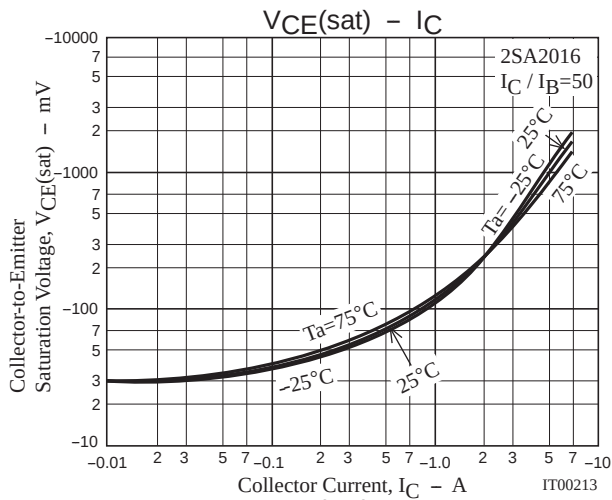
$$I_C=20I_{B1}=-20I_{B2}=2.5\text{A}$$

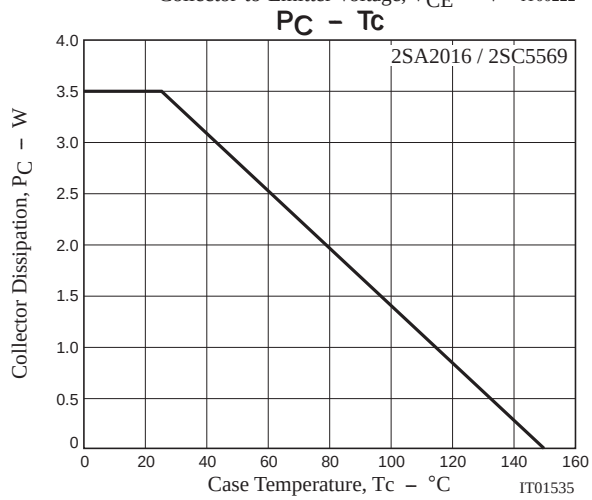
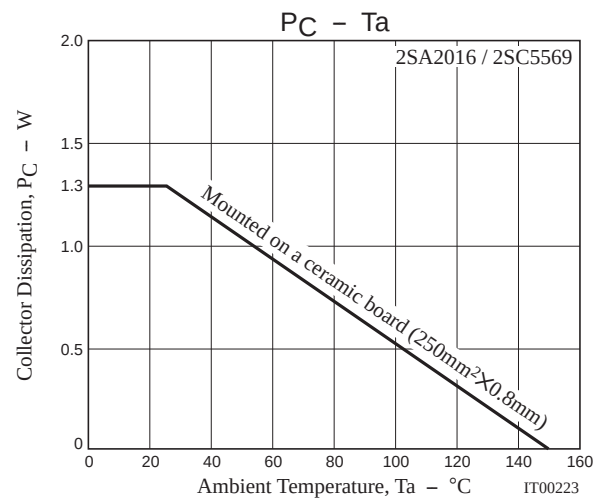
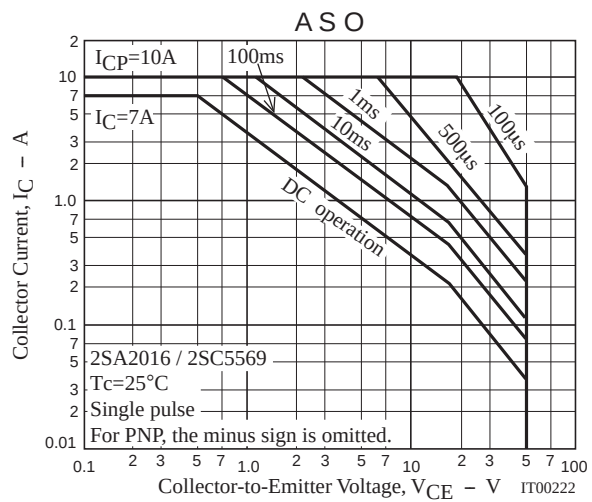
For PNP, the polarity is reversed.

Ordering Information

Device	Package	Shipping	memo
2SA2016-TD-E	PCP	1,000pcs./reel	Pb Free
2SC5569-TD-E	PCP	1,000pcs./reel	

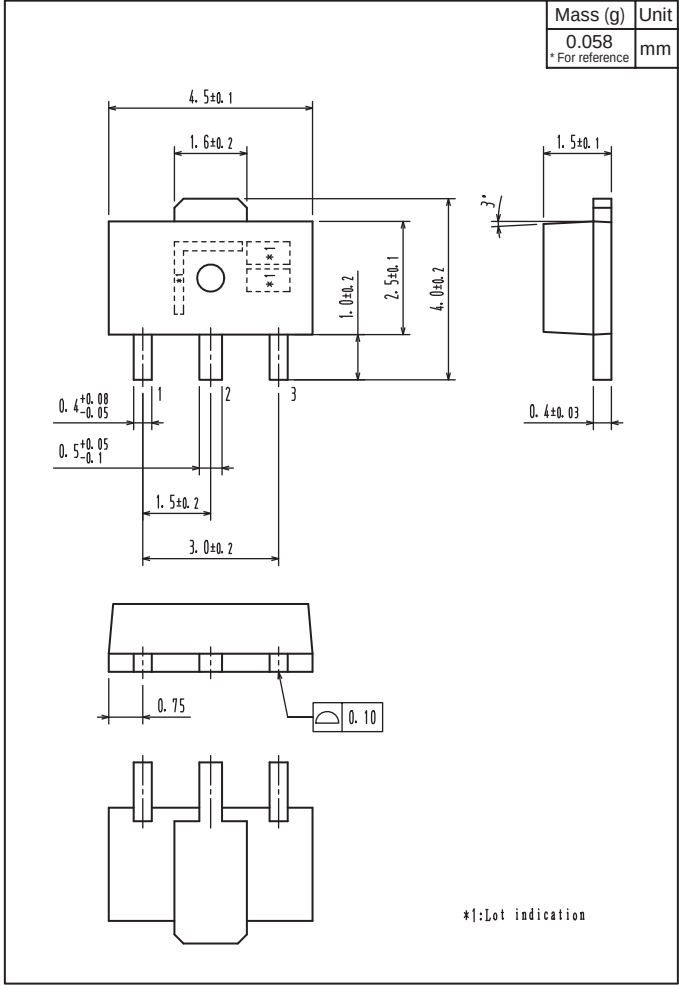




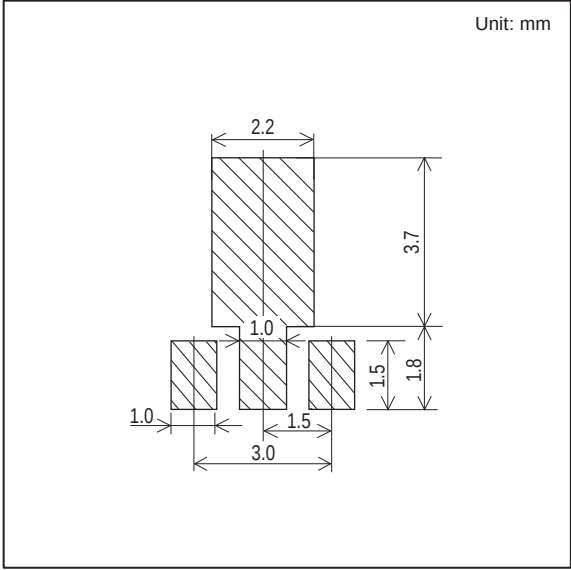


Outline Drawing

2SA2016-TD-E, 2SC5569-TD-E



Land Pattern Example



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